

## Features

- Compliant to LIN 2.0, LIN 2.1, LIN 2.2, LIN 2.2A and ISO 17987-4 Electrical Physical Layer (EPL) Specification
- Compliant to SAE J2602 LIN Network for Vehicle Applications
- Support LIN Data Rates up to 20 Kbps
- Wide V<sub>BAT</sub> Input Voltage Range Supports 5.5 V to 40 V
- Low-current Standby Mode and Sleep Mode with Bus Wake-up and Local Wake-up Capability
- Input Levels Compatible with 3.3 V and 5 V MCU Interface
- System-level Power Control with INH Pin
- Ideal Passive Behavior to LIN Bus when Unpowered
- Integrated Pull-up Resistor for LIN Slave Applications
- Protection Feature:
  - Bus pin IEC 61000-4-2 ESD Protection ±15 kV
  - Bus Fault Tolerant: ±45 V
  - VBAT Undervoltage Protection
  - TXD Dominant Time-out Function
  - Thermal Shutdown Protection
- Available in SOP8 Package and Leadless DFN3X3-8L Package with Improved Automated Optical Inspection (AOI) Capability
- AEC-Q100 Qualified for Automotive Applications, Grade 1

# Applications

- Automotive and Transportation
- Body Electronics / Lighting
- Power Train / Chassis
- Infotainment / Cluster
- ADAS / Safety

## Description

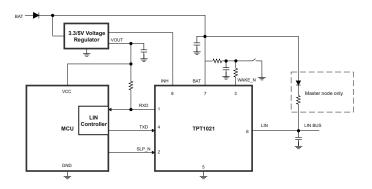
The TPT1021 is a local interconnect network (LIN) physical layer transceiver that is compliant to ISO 17987-4, SAE J2602 and LIN 2.0, LIN 2.1, LIN 2.2, and LIN 2.2A physical layer standard. LIN is a low-speed universal asynchronous receiver transmitter (UART) communication protocol that supports automotive in-vehicle sub-networks.

The device supports LIN networks up to 20 Kbps with the enhanced timing margin. The device converts the transmitted data received at the TXD with the optimized slew rate to minimize the electro-magnetic emission (EME) and reports the state of the LIN bus at the RXD.

As designed, the device features overvoltage and loss of ground protection from -45 V to +45 V, over-temperature shutdown. The device has low-current standby and sleep mode with LIN BUS wake-up and local wake-up capability via the WAKE\_N pin. The INH pin of the device is used to control voltage regulation to reduce system-level power consumption. The device integrates a pull high resistor for LIN slave applications and ESD protection which allows applications to operate with a reduced dependence on external components. Additionally, all devices include many protection features to enhance the device and network robustness.

The TPT1021 is available in SOP-8 and DFN3X3-8L packages and is characterized from  $-40^{\circ}$ C to  $+125^{\circ}$ C.

# **Typical Application Circuit**





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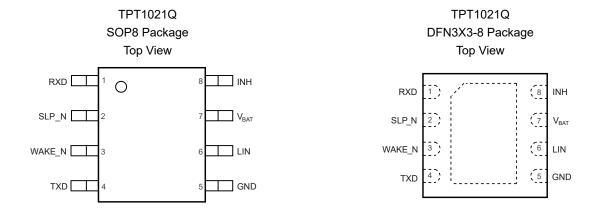


# **Revision History**

Date	Revision	Notes
2022-12-05	Rev.Pre.0	Initial version
2024-1-05	Rev.A.0	Released version



# **Pin Configuration and Functions**



#### Table 1. Pin Functions: TPT1021Q

Р	in	1/0	Description			
No.	Name	I/O	Description			
1	RXD	Output	LIN receives data output			
2	SLP_N	Input	Sleep mode control input, active low			
3	WAKE_N	HV Input	Local wake-up Input, active low			
4	TXD	Input	LIN transmits data input			
5	GND	GND	Ground			
6	LIN	BUS I/O	LIN Bus input/output line			
7	VBAT	Power	High voltage power supply from the battery			
8	INH	HV Output	Inhibit output to control external voltage regulators			



# **Specifications**

### **Absolute Maximum Ratings**

	Parameter	Conditions	Min	Max	Unit
V <sub>BAT</sub>	Battery Supply Voltage Range		-0.3	45	V
V <sub>TXD</sub>	Pin TXD Voltage Range		-0.3	7	V
V <sub>RXD</sub>	Pin RXD Voltage Range		-0.3	7	V
V <sub>SLP_N</sub>	Pin SLP_N Voltage Range		-0.3	7	V
V <sub>WAKE_N</sub>	Pin WAKE_N Voltage Range		-0.3	45	V
VINH	Pin INH Voltage Range		-0.3	45	V
V <sub>LIN</sub>	Pin LIN Voltage Range	With respect to GND	-45	45	V
TJ	Junction Temperature <sup>(2)</sup>		-40	150	°C
T <sub>STG</sub>	Storage Temperature		-55	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

(2) This data was taken with the JEDEC standard multilayer test boards.

### ESD (Electrostatic Discharge Protection)

	Parameter	Condition	Min	Мах	Unit
	Electrostatics Discharge <sup>(1)(2)</sup>	IEC61000-4-2 (150 pF, 330 Ω discharge circuit), contact discharge on LIN, WAKE_N, INH Pins	-15	15	kV
VESD		Human Body Model (HBM) on LIN, WAKE_N, INH pins	-15	15	kV
		Human Body Model (HBM) on any other pins	-6	6	kV
		Charged Device Model (CDM) on all pins	-1.5	1.5	kV
	Transient Immunity ISO 7637-2 on	Pulse1	-100		V
V		Pulse2a		75	V
V <sub>TRAN</sub>	Bus Pins	Pulse3a	-150		V
		Pulse3b		100	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



## **Recommended Operating Conditions**

	Parameter	Min	Мах	Unit
V <sub>BAT</sub>	Battery Power Supply	5.5	40	V
V <sub>LIN</sub>	LIN Bus Input Voltage	0	40	V
V <sub>WAKE_N</sub>	WAKE_N Pin Input Voltage	0	40	V
VLOGIC	Logic Pin Voltage	0	5.25	V
TJ	Operating Virtual Junction Temperature Range	-40	150	°C

### **Thermal Information**

Package Type	θιΑ	θις	Unit
SOP8	118	48	°C/W
DFN3x3-8	51	23	°C/W



### **Electrical Characteristics**

All test conditions:  $V_{BAT}$  = 5.5 V to 40 V,  $R_L$ = 500  $\Omega$ ,  $T_A$  = -40°C to 125°C, typical values are tested at  $V_{BAT}$  = 12 V, unless otherwise noted.

	Parameter	Conditions	Min	Тур	Мах	Unit
Pin VBAT	-			1		
Vth_vbat_ l	Low Level of VBAT UVLO Threshold Voltage		3.50	4.30		V
Vth_vbat_ h	High Level of VBAT UVLO Threshold Voltage			4.45	5.20	V
Vhys_vbat	Hysteresis Voltage on Power-on Reset <sup>(1)</sup>			0.15		V
	Sleep Mode Supply Current	$V_{LIN} = V_{BAT}; V_{WAKE_N} = V_{BAT};$ $V_{TXD} = 0 V; V_{SLP_N} = 0 V$		5.9	11	μA
IBAT	Standby Mode Supply	Recessive; $V_{INH} = V_{BAT}$ ; $V_{LIN} = V_{BAT}$ ; $V_{WAKE_N} = V_{BAT}$ ; $V_{TXD} = 5$ V; $V_{SLP_N} = 0 V$		21	30	μA
	Current	Dominant; $V_{INH} = V_{BAT}$ ; $V_{LIN} =$ 0 V; $V_{WAKE_N} = V_{BAT}$ ; $V_{TXD} = 0$ V; $V_{SLP_N} = 0 V$		440	1900	μA
	Normal Mode Supply Current	Recessive; $V_{INH} = V_{BAT}$ ; $V_{LIN} = V_{BAT}$ ; $V_{WAKE_N} = V_{BAT}$ ; $V_{TXD} = 5$ V; $V_{SLP_N} = 5$ V		157	280	μΑ
		Dominant; $V_{INH} = V_{BAT}$ ; $V_{LIN} =$ 0 V; $V_{WAKE_N} = V_{BAT}$ ; $V_{TXD} = 0$ V; $V_{SLP_N} = 5 V$		1.6	5.6	mA
Pin TXD						
Vін	High-Level Input Voltage		2		7	V
VIL	Low-Level Input Voltage		-0.3		0.8	V
Vhys_txd	Hysteresis Voltage on Pin TXD		50	200	400	mV
R <sub>PD_TXD</sub>	Pin TXD Pull down Resistance	V <sub>TXD</sub> = 5 V	140	500	1200	kΩ
IIL	Low-Level Input Current	V <sub>TXD</sub> = 0 V	-5		5	μA
lol	Low-Level Output Current	Local wake-up request; Standby mode; V <sub>WAKE_N</sub> = 0 V; V <sub>LIN</sub> = V <sub>BAT</sub> ; VTXD = 0.4 V	1.5	3.5		mA



	Parameter	Conditions	Min	Тур	Мах	Unit
VIH	High-Level Input Voltage		2		7	V
VIL	Low-Level Input Voltage		-0.3		0.8	V
Vhys_slp_ n	Hysteresis Voltage on Pin SLP_N		50	200	400	mV
R <sub>PD_SLP_N</sub>	Pin SLP_N Pull-down Resistance	V <sub>TXD</sub> = 5 V	140	500	1200	kΩ
IIL	Low-Level Input Current	V <sub>TXD</sub> = 0 V	-5		5	μA
Pin RXD						
I <sub>OL</sub>	Low-Level Output Current	Normal mode; $V_{LIN} = 0 V$ , $V_{RXD} = 0.4 V$	1.5	4.2		mA
I <sub>LH</sub>	High-Level Leakage Current	Normal mode; $V_{LIN} = V_{BAT}$ , $V_{RXD} = 5 V$	-5	0	5	μA
Pin WAKE	E_N					
VIL	Low-Level Input Voltage		-0.3		V <sub>BAT</sub> - 3.3	V
I <sub>PU_L</sub>	Low-Level Pull-up Current	V <sub>WAKE_N</sub> = 0 V	-30	-12	-1	μA
Ін	High-Level Leakage Current		-5	0	5	μA
Pin INH						
$\Delta V_{\text{INH}}$	High-Level voltage drop INH with respect to V <sub>BAT</sub>	I <sub>INH</sub> = -0.5mA		0.7	1	V
ILH	High-Level Leakage Current	Sleep mode; V <sub>INH</sub> = 0 V ;	-5	0	5	μA
Pin LIN						
I <sub>BUS_LIM</sub>	Dominant Output Current Limitation	V <sub>BAT</sub> = V <sub>LIN</sub> = 18V; V <sub>TXD</sub> = 0 V	40		160	mA
R <sub>PU</sub>	Pull-up Resistance	Sleep mode; V <sub>SLP_N</sub> = 0 V	50	160	250	kΩ
I <sub>BUS_PAS_R</sub> EC	Receiver Recessive Input Leakage Current	V <sub>BAT</sub> = 5.5 V; V <sub>LIN</sub> = 27 V; V <sub>TXD</sub> = 5 V			20	μA
I <sub>BUS_PAS_D</sub>	Receiver Dominant Input Leakage Current	Normal mode; $V_{BAT} = 12 V$ ; $V_{LIN} = 0 V$ ; $V_{TXD} = 5 V$	-600			μA
VSerDiode	Voltage Drop at the Serial Diode <sup>(1)</sup>	Pull-up path with $R_{SLAVE}$ ; I <sub>SerDiode</sub> = 10 $\mu$ A	0.4		1	V
I <sub>BUS_NO_G</sub> ND	Ground Loss Bus Current	V <sub>BAT</sub> = 40 V; V <sub>LIN</sub> = 0 V	-750		10	μA
I <sub>BUS_NO_B</sub> AT	Battery Loss Bus Current	V <sub>BAT</sub> = 0 V; V <sub>LIN</sub> = 40 V			40	μA
V <sub>BUS_DOM</sub>	Receiver Dominant				0.4 x V <sub>BAT</sub>	V
V <sub>BUS_REC</sub>	Receiver Recessive		0.6 x V <sub>BAT</sub>			V
V <sub>BUS_CNT</sub>	Receiver Center Voltage		0.475 x V <sub>BAT</sub>	0.5 x V <sub>BAT</sub>	0.525 x V <sub>BAT</sub>	V
V <sub>HYS</sub>	Receiver Hysteresis Voltage				0.175 x V <sub>BAT</sub>	V
R <sub>SLAVE</sub>	Slave Resistance	Between LIN and V <sub>BAT</sub> ; V <sub>BAT</sub> = 12 V; V <sub>LIN</sub> = 0 V	20	30	47	kΩ



	Parameter	Conditions	Min	Тур	Мах	Unit
C <sub>LIN</sub>	Pin LIN Capacitance <sup>(1)</sup>				30	pF
Vo_rec	Recessive Output Voltage	Normal mode; V <sub>TXD</sub> = V <sub>CC</sub> ;	$0.85 \text{ x } V_{BAT}$			V
Vo_dom	Dominant Output Voltage	Normal mode; V <sub>TXD</sub> = 0 V;			1.4	V
Temperat	ture Detection					
T <sub>J_SD</sub>	Shutdown Junction Temperature		160	180	200	°C
Tj_sd_r	Recover Shutdown Junction Temperature		125		160	°C



## **Duty Cycles**

All test conditions:  $V_{BAT}$ = 5.5 V to 40 V,  $R_L$ = 500  $\Omega$ ,  $T_A$ = -40°C to 125°C, see Figure 2, unless otherwise noted.

Param	eter	Conditions	Min	Тур	Max	Unit
D1	Duty cycle 1; D1= t <sub>BUS_REC_MIN</sub> / 2 x t <sub>BIT</sub>	$V_{TH\_REC\_MAX} = 0.744 \text{ x } V_{BAT};$ $V_{TH\_DOM\_MAX} = 0.581 \text{ x } V_{BAT};$ $20 \text{ kbps; } t_{BIT} = 50  \mu\text{s};$ $7 \text{ V} \leq V_{BAT} \leq 40 \text{ V}$	0.396			
D1	Duty cycle 1; D1= t <sub>BUS_REC_MIN</sub> / 2 x t <sub>BIT</sub>	V <sub>TH_REC_MAX</sub> = 0.744 x V <sub>BAT</sub> ; V <sub>TH_DOM_MAX</sub> = 0.581 x V <sub>BAT</sub> ; 20 kbps; t <sub>BIT</sub> = 50 µs; 5.5 V ≤ V <sub>BAT</sub> < 7 V	0.396			
D2	Duty cycle 2; D2= t <sub>BUS_REC_MAX</sub> / 2 x t <sub>BIT</sub>	V <sub>TH_REC_MIN</sub> = 0.422 x V <sub>BAT</sub> ; V <sub>TH_DOM_MIN</sub> = 0.284 x V <sub>BAT</sub> ; 20 kbps; t <sub>BIT</sub> = 50 µs; 7.6 V ≤ V <sub>BAT</sub> ≤ 40 V			0.581	
D2	Duty cycle 2; D2= t <sub>BUS_REC_MAX</sub> / 2 x t <sub>BIT</sub>	V <sub>TH_REC_MIN</sub> = 0.464 x V <sub>BAT</sub> ; V <sub>TH_DOM_MIN</sub> = 0.312 x V <sub>BAT</sub> ; 20 kbps; t <sub>BIT</sub> = 50 µs; 5.5 V ≤ V <sub>BAT</sub> < 7.6 V			0.581	
D3	Duty cycle 3; D3= t <sub>BUS_REC_MIN</sub> / 2 x t <sub>BIT</sub>	V <sub>TH_REC_MAX</sub> = 0.778 x V <sub>BAT</sub> ; V <sub>TH_DOM_MAX</sub> = 0.616 x V <sub>BAT</sub> ; 10.4 kbps; t <sub>BIT</sub> = 96 µs; 7 V ≤ V <sub>BAT</sub> ≤ 40 V	0.417			
D3	Duty cycle 3; D3= t <sub>BUS_REC_MIN</sub> / 2 x t <sub>BIT</sub>	V <sub>TH_REC_MAX</sub> = 0.778 x V <sub>BAT</sub> ; V <sub>TH_DOM_MAX</sub> = 0.616 x V <sub>BAT</sub> ; 10.4 kbps; t <sub>BIT</sub> = 96 µs; 5.5 V ≤ V <sub>BAT</sub> < 7 V	0.417			
D4	Duty cycle 4; D4= t <sub>BUS_REC_MAX</sub> / 2 x t <sub>BIT</sub>	$ \begin{array}{l} V_{TH\_REC\_MIN} = 0.389 \ x \ V_{BAT}; \\ V_{TH\_DOM\_MIN} = 0.251 \ x \ V_{BAT}; \\ 10.4 \ kbps; \ t_{BIT} = 96 \ \mu s; \\ 7.6 \ V \leq V_{BAT} \leq 40V \end{array} $			0.590	
D4	Duty cycle 4; D4= t <sub>BUS_REC_MAX</sub> / 2 x t <sub>BIT</sub>	V <sub>TH_REC_MIN</sub> = 0.389 x V <sub>BAT</sub> ; V <sub>TH_DOM_MIN</sub> = 0.251 x V <sub>BAT</sub> ; 10.4 kbps; t <sub>BIT</sub> = 96 µs; 5.5 V ≤ V <sub>BAT</sub> < 7.6 V			0.590	



### **AC Timing Requirements**

All test conditions:  $V_{BAT}$  = 5.5 V to 40 V,  $R_L$  = 500  $\Omega$ ,  $T_A$  = -40°C to 125°C, typical values are tested at  $V_{BAT}$  = 12V, unless otherwise noted.

	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>F</sub>	LIN Bus Fall Time	$C_{BUS}$ = 1 nF, $R_{BUS}$ = 1 k $\Omega$ ; $C_{BUS}$ = 6.8 nF, $R_{BUS}$ = 660 $\Omega$ ; $C_{BUS}$ = 10 nF, $R_{BUS}$ = 500 $\Omega$ ;			22.5	μs
t <sub>R</sub>	LIN Bus Rise Time	$C_{BUS}$ = 1 nF, $R_{BUS}$ = 1 kΩ; $C_{BUS}$ = 6.8 nF, $R_{BUS}$ = 660 Ω; $C_{BUS}$ = 10 nF, $R_{BUS}$ = 500 Ω;			22.5	μs
$\Delta t_{(R-F)}$	Difference between LIN Bus Rise-and-Fall Time	V <sub>BAT</sub> = 7.3 V	-5		5	μs
t <sub>TX_PD</sub>	Transmitter Propagation Delay	Rising and falling			6	μs
t <sub>TX_SYM</sub>	Transmitter Propagation Delay Symmetry		-3		3	μs
t <sub>RX_PD</sub>	Receiver Propagation Delay	Rising and falling			6	μs
t <sub>RX_SYM</sub>	Receiver Propagation Delay Symmetry		-2		2	μs
twake_dom_lin	LIN Dominant Wake-up Time	Sleep mode	30	80	150	μs
twake_dom_wake	Pin WAKE_N Dominant Wake-up Time	Sleep mode	7	25	50	μs
tgotonorm	Go-to-Normal Time	Mode change time from Sleep, Power-on, Standby mode into Normal mode	2	5	10	μs
tinitnorm	Normal Mode Initialization Time <sup>(1)</sup>		5	12	20	μs
tGOTOSLEEP	Go-to-Normal Time	Mode change time from Normal to Sleep mode	2	5	10	μs
t <sub>то_дом_тхд</sub>	TXD dominant time-out time	V <sub>TXD</sub> = 0 V	27	43	90	ms

(1) The data is based on bench tests and design simulations.



## **Parameter Measurement Information**

### **Test Circuit**

**Parameter Diagram** 

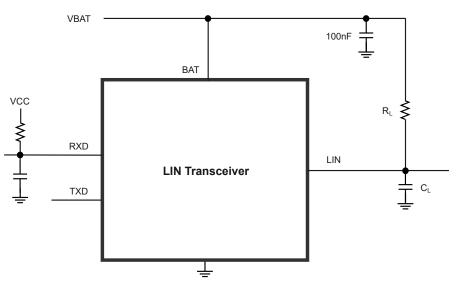
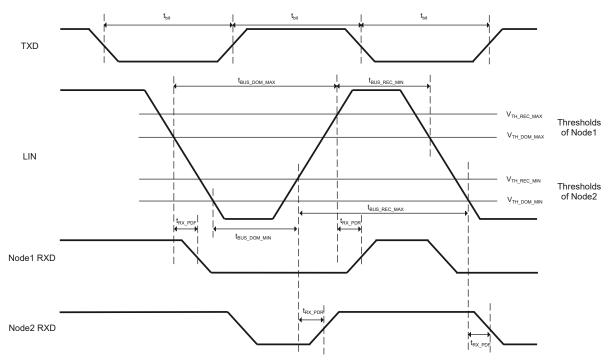


Figure 1. LIN Transceiver Timing Parameter Test Circuit



#### Figure 2. LIN Transceiver Timing Diagram



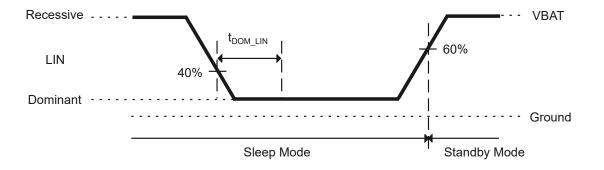


Figure 3. Remote wake-up diagram



## **Detailed Description**

### Overview

The TPT1021 is a local interconnect network (LIN) physical layer transceiver that is compliant with ISO 17987-4, SAE J2602 and LIN 2.0, LIN 2.1, LIN 2.2, and LIN 2.2A physical layer standards. LIN is a low-speed universal asynchronous receiver transmitter (UART) communication protocol that supports automotive in-vehicle sub-networks. The device supports LIN networks up to 20 Kbps with the enhanced timing margin. The device converts the transmitted data received at the TXD with the optimized slew rate to minimize the electro-magnetic emission (EME) and reports the state of the LIN bus at the RXD. As designed, the device features overvoltage and loss of ground protection from -45 V to +45 V, over-temperature shutdown. The device has low-current standby and sleep mode with LIN BUS wake-up and local wake-up capability via the WAKE\_N pin. The INH pin of the device is used to control voltage regulation to reduce system-level power consumption. The device integrates a pull high resistor for LIN slave applications and ESD protection which allows applications to operate with a reduced dependence on external components. Additionally, all devices include many protection features to enhance the device and network robustness. The TPT1021 is available in SOP-8 and DFN3X3-8L packages and is characterized from  $-40^{\circ}$ C to  $+125^{\circ}$ C.

#### RXD C 8 **Bus Timer** O INH VBAT/2 Mode 7 Change Power Manage Unit -O VBAT Timer VBAT WAKE Wakeup CONTROL Timer 6 -0 I IN Dominant TXD O Timeout 5 Timer O GND Ī ≷ **TPT1021**

### Functional Block Diagram

Figure 4. Functional Block Diagram

### Feature Description

### **Device Operating Modes**

The TPT1021 supports modes for Normal mode, Power-on mode, Standby mode, and Sleep mode. The figure below shows the state diagram.



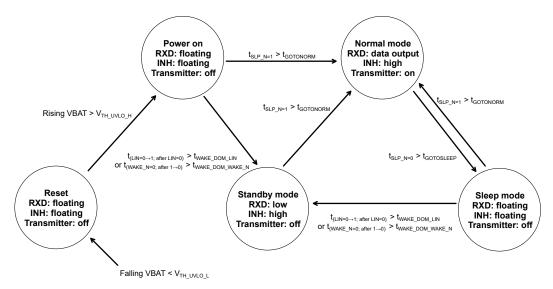


Figure 5. Functional Block Diagram

Table 2. Function Table

Mode	SLP_N	TXD	RXD	INH	Transmitter	Comments
Normal	High	High: recessive state Low: dominant state	High: recessive state Low: dominant state	High	Normal	
Sleep	Low	Weak pull-down	Floating	Floating	Off	No wake-up event detected
Standby	Low	Weak pull-down if remote wake-up; strong pull-down if local wake-up	Low	High	Off	Wake-up event detected
Power- on	Low	Weak pull-down	Floating	High	Off	

#### Normal Mode

In Normal mode, the TPT1021 can transmit and receive data through the LIN bus line. The receiver detects the data stream at the LIN bus input pin and transfers it to the microcontroller via the RXD pin. On the bus, a HIGH level corresponds to a recessive state, while a LOW level represents a dominant state. The receiver incorporates a voltage-dependent threshold with hysteresis and an integrated filter to suppress noise on the bus.

The transmit data stream from the protocol controller at the TXD input is converted by the transmitter into a bus signal with optimized slew rate and wave shaping, aiming to minimize electromagnetic emissions (EME). The LIN bus output pin is pulled HIGH through an internal slave termination resistor. For master applications, an external resistor in series with a diode should be connected between pin INH or VBAT and pin LIN.

#### Sleep Mode

The TPT1021 offers an energy-efficient mode known as the power-saving mode. Despite its extremely low current consumption, the TPT1021 retains the capability to be remotely awakened via the LIN pin, locally awakened via the WAKE\_N pin, or directly activated through the SLP\_N pin. Input filters are incorporated at the receiver (LIN), WAKE\_N pin, and SLP\_N pin to prevent undesired wake-up events caused by automotive transients or electromagnetic interference (EMI).

To initiate Sleep mode from Normal mode, a falling edge on the SLP\_N pin is required. In order to successfully enter Sleep mode (INH pin becomes floating), the sleep command (SLP\_N pin set to LOW) must be sustained for a minimum duration of t<sub>gotosleep</sub>.

During Sleep mode, the internal slave termination between the LIN and VBAT pins is disabled to minimize power dissipation if the LIN pin is short-circuited to ground. Only a weak pull-up is present between the LIN and VBAT pins.

#### Standby Mode

Whenever a local or remote wake-up occurs while the TPT1021 is in Sleep mode, Standby mode is automatically activated. These wake-up events trigger the activation of pin INH and enable the slave termination resistor at the LIN pin. Consequently, the voltage regulator and microcontroller can be powered on due to the HIGH condition on pin INH.

Standby mode is indicated by a low level on the RXD pin, which can serve as an interrupt for the microcontroller.

During Standby mode (with pin SLP\_N still low), the state of the TXD pin (weak pull-down or strong pull-down) indicates the source of the wake-up: a weak pull-down for a remote wake-up request and a strong pull-down for a local wake-up request.

#### Wake-up

When VBAT voltage exceeds the undervoltage threshold voltage, the TPT1021 transitions into Power-on mode. In this mode, despite being powered up and INH being high, both the transmitter and receiver remain inactive. If SLP\_N is HIGH for a duration greater than  $t_{GOTONORM}$ , the TPT1021 enters Normal mode.

To wake up a TPT1021 that is in Sleep mode, there are three methods:

Remote wake-up through the LIN bus by transmitting a dominant bus state that is sustained for a duration of at least  $t_{WAKE\_DOM\_LIN}$  then followed by a rising edge.

Local wake-up by a negative edge signal at the WAKE\_N pin and sustain low for a duration of at least twake\_DOM\_WAKE\_N. This transition triggers the wake-up event and brings the TPT1021 out of Sleep mode.

Mode change by setting the SLP\_N pin to a HIGH level. This change in pin state signals the TPT1021 to exit Sleep mode and enter Normal mode.

#### Wake-up Source Recognition

The TPT1021 is capable of distinguishing between a local wake-up request, initiated on pin WAKE\_N, and a remote wake-up request through a dominant bus state. A local wake-up request activates the wake-up source flag, which can be accessed on pin TXD during Standby mode. If an external pull-up resistor is connected to pin TXD, a HIGH level indicates a remote wake-up request (with a weak pull-down at pin TXD), while a LOW level indicates a local wake-up request (with a strong pull-down at pin TXD, considerably stronger than the external pull-up resistor).

Both the wake-up request flag (indicated on pin RXD) and the wake-up source flag (indicated on pin TXD) reset immediately after the MCU sets pin SLP\_N to a HIGH state.

#### **Protection Features**

#### TXD Dominant Time-out

The device will detect TXD dominant time-out and prevent a permanent low on the TXD pin driving the LIN bus into permanent dominant blocking the LIN bus network. If the TXD remains low for longer than  $t_{TXD_DTO}$ , the transmitter will be disabled until the fault flag has been cleared.

#### Under-voltage Lockout (UVLO)

The device integrated under-voltage detect and lockout circuit of the supply terminal to keep the device in protected mode if the supply voltage drops below the threshold until the supply voltage is higher than the UVLO threshold. This protects the device and system during undervoltage events on supply terminals.



#### **Over-Temperature Protection (OTP)**

The output drivers are protected against over-temperature conditions. If the virtual junction temperature exceeds the shutdown junction temperature  $T_{J\_SD}$ , the output drivers will be disabled until the virtual junction temperature falls below  $T_{J\_SD\_R}$  and TXD becomes recessive again. Including the TXD condition ensures that output driver oscillation due to temperature drift is avoided.

#### Fail-safe Features

An internal pull-down to GND on the TXD pin to establish a predetermined level in case the TXD pin is disconnected.

An internal pull-down to GND on the SLP\_N pin to establish a predetermined level in case the SLP\_N pin is disconnected.

RXD pin is set floating when the VBAT pin is unpowered.

Current limit is applied to LIN transmitter output to protect LIN bus short circuits to VBAT or GND.

VBAT and GND loss will not impact the LIN bus or the MCU. No reverse current flows from the bus into the LIN pin. The internal integrated LIN slave termination resistor remains keeping the current path from VBAT to LIN. Disconnecting the LIN transceiver from the power supply does not affect the LIN bus.



## **Application and Implementation**

Note

Information in the following application sections is not part of the 3PEAK's component specification and 3PEAK does not warrant its accuracy or completeness. 3PEAK's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## **Typical Application**

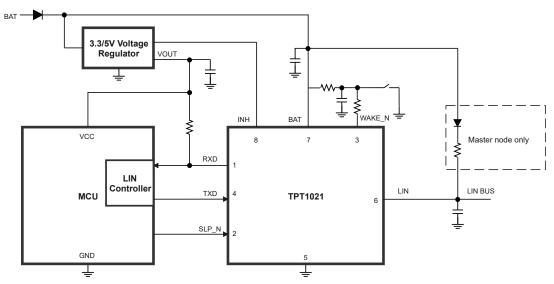
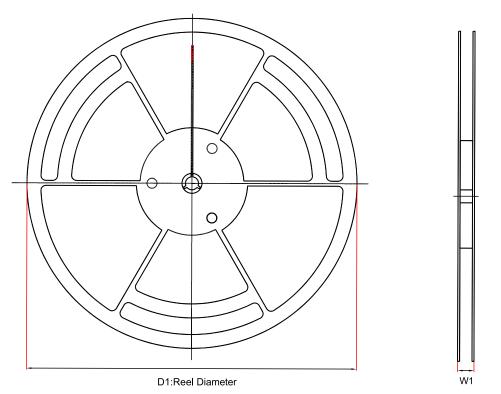
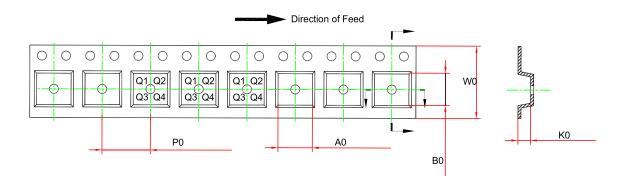


Figure 6. Typical Application Circuit



# Tape and Reel Information



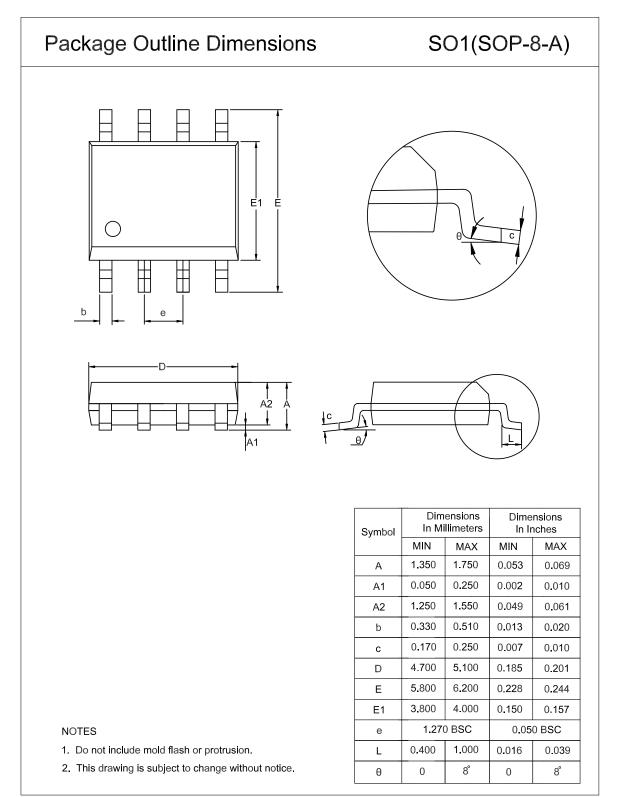


Order Number	Package	D1 (mm)	A0 (mm)	K0(mm)	W0 (mm)	W1 (mm)	B0 (mm)	P0 (mm)	Pin1 Quadrant
TPT1021Q- SO1R-S	SOP8	330	6.5	2	12	17.6	5.4	8	Q1
TPT1021Q- DFCR-S	DFN3x3-8	330	3.3	1.1	12	17.6	3.3	8	Q1



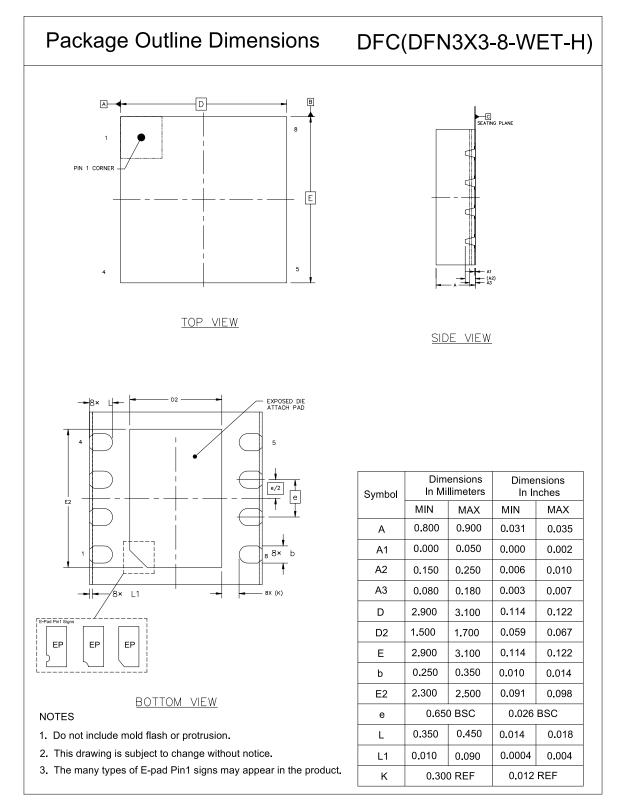
## Package Outline Dimensions

### SOP8





#### DFN3X3-8





## **Order Information**

Order Number	Operating Temperature Range	Package	Marking Information	MSL	Transport Media, Quantity	Eco Plan
TPT1021Q-SO1R-S	−40 to 125°C	SOP8	1021Q	MSL1	Tape and Reel, 4000	Green
TPT1021Q-DFCR-S	−40 to 125°C	DFN3x3-8	1021Q	MSL1	Tape and Reel, 4000	Green

Green: 3PEAK defines "Green" to mean RoHS compatible and free of halogen substances.



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# **TPT1021Q**

Automotive Fault Protected LIN Transceiver with WAKE and INH

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